

Abstract of the Disclosure

Standard post-etch photoresist clean procedures for porous dielectric materials manufacturing may involve wet cleans in which a solvent is used for polymer residue removal. In many cases, the components of the solvent are absorbed into porous film layers and can later volatilize during subsequent metal deposition steps. A low pressure anneal of limited duration and high temperature, performed after the wet clean and prior to metal deposition, satisfactorily removes the absorbed components.